

VS-16TTS08FP-M3, VS-16TTS12FP-M3

Vishay Semiconductors

High Voltage Phase Control Thyristor, 16 A



PRIMARY CHARACTERISTICS					
I _{T(AV)} 10 A					
V _{DRM} /V _{RRM}	800 V, 1200 V				
V _{TM}	1.4 V				
I _{GT}	60 mA				
TJ	-40 °C to 125 °C				
Package	3L TO-220 FullPAK				
Circuit configuration	Single SCR				

FEATURES

· Designed and gualified for industrial level

Fully isolated package (V_{INS} = 2500 V_{RMS})



HALOGEN · Material categorization: for definitions of FREE compliance please see www.vishay.com/doc?99912

APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-16TTS..FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS				
Capacitive input filter $T_A = 55 \text{ °C}$, $T_J = 125 \text{ °C}$, common heatsink of 1 °C/W	13.5	17	A				

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
I _{T(AV)}	Sinusoidal waveform	10	A				
I _{RMS}		16	A				
V _{DRM} /V _{RRM}		800, 1200	V				
I _{TSM}		200	A				
V _T	10 A, T _J = 25 °C	1.4	V				
dV/dt		500	V/µs				
dl/dt		150	A/µs				
TJ	Range	-40 to 125	٥°				

VOLTAGE RATINGS							
VRRM, MAXIMUM PEAK VDRM, MAXIMUM PEAK IRRM/IDRM PART NUMBER REVERSE VOLTAGE DIRECT VOLTAGE AT 125 °C V V MA							
VS-16TTS08FP-M3	800 800 10						
VS-16TTS12FP-M3	1200	1200	10				

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COMPLIANT



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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL		TEST CONDITIONS		UES	
PANAMEIEN	STMBOL		TEST CONDITIONS			onno
Maximum average on-state current	I _{T(AV)}	T _C = 70 °C, ⁻	180° conduction, half sine wave	10		
Maximum RMS on-state current	I _{RMS}			1	6	А
Maximum peak, one-cycle,	1	10 ms sine p	oulse, rated V _{RRM} applied	1	70	А
non-repetitive surge current	I _{TSM}	10 ms sine p	ulse, no voltage reapplied	2	00	
Moving up 12t for fusing	l ² t	10 ms sine p	oulse, rated V _{RRM} applied	144		A ² s
Maximum I ² t for fusing	I-t	10 ms sine p	10 ms sine pulse, no voltage reapplied		200	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10	ms, no voltage reapplied	2000		A²√s
Maximum on-state voltage drop	V _{TM}	10 A, T _J = 25	10 A, T _J = 25 °C		.4	V
On-state slope resistance	r _t	T 405 %Q		24	1.0	mΩ
Threshold voltage	V _{T(TO)}	T _J = 125 °C		1	.1	V
Movimum reverse and direct lookage ourrent	1 /1	T _J = 25 °C		0	.5	
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	V _R = Rated V _{RRM} /V _{DRM}	1	0	
Holding current	Ι _Η	Anode supply = 6 V, resistive load, initial $I_T = 1 A$ 16TTS08FP, 16TTS12FP, $T_J = 25 \text{ °C}$		-	150	mA
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$		2	00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linear to 80 %, $V_{DRM} = R_g - k = Open$	5	00	V/µs
Maximum rate of rise of turned-on current	dl/dt			1	50	A/µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	w	
Maximum average gate power	P _{G(AV)}		2.0	~~~	
Maximum peak positive gate current	+ I _{GM}		1.5	А	
Maximum peak negative gate voltage	- V _{GM}		10	V	
	I _{GT}	Anode supply = 6 V, resistive load, T_J = -10 °C	90		
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	60	mA	
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	35		
		Anode supply = 6 V, resistive load, T_J = -10 °C	3.0		
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	2.0	v	
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	1.0	v	
Maximum DC gate voltage not to trigger	V _{GD}				
Maximum DC gate current not to trigger	I _{GD}	$T_{J} = 125 \text{ °C, } V_{DRM} = \text{Rated value} $ 2.0		mA	

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9				
Typical reverse recovery time	t _{rr}	T.I = 125 °C	4	μs			
Typical turn-off time	tq	1j = 125 C	110				

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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to +125	°C
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	2.5	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth, and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	oz.
Mounting torque	minimum			6 (5)	kgf ⋅ cm
Mounting torque	maximum			12 (10)	(lbf · in)
· · · · · ·				16TTS	08FP
warking device	Marking device		Case style 3L TO-220 FullPAK	16TTS12FP	

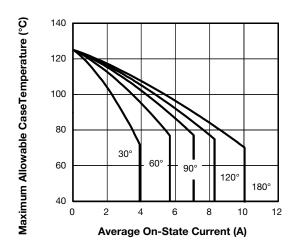
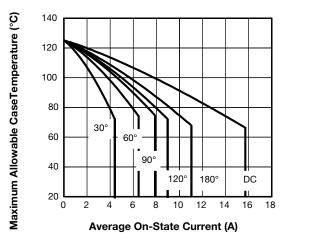
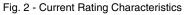


Fig. 1 - Current Rating Characteristics





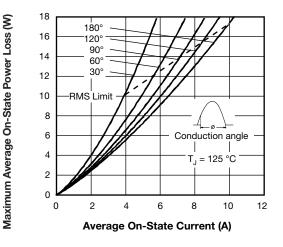


Fig. 3 - On-State Power Loss Characteristics

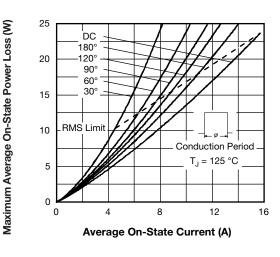


Fig. 4 - On-State Power Loss Characteristics

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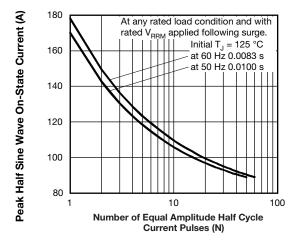


Fig. 5 - Maximum Non-Repetitive Surge Current

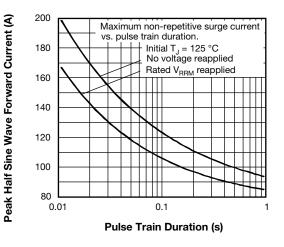


Fig. 6 - Maximum Non-Repetitive Surge Current

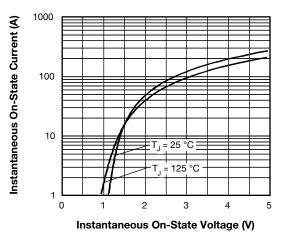


Fig. 7 - On-State Voltage Drop Characteristics

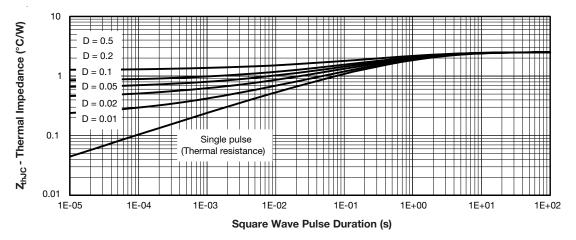
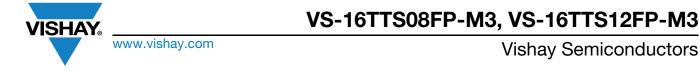


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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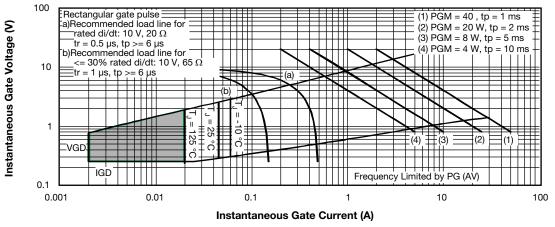


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	16	т	т	S	12	FP	-M3	
		(2)	(3)	4	(5)	(6)	(7)	(8)	
	1	· Vish	ay Sem	iconduc	tors pro	duct	0	\bigcirc	
	2 -		•	ng, RMS	•				
	3 -	Circ	uit confi	guratior	1:				
		T =	single th	nyristor					
	4 -	Pac	kage:						
	_		TO-220						
	5 -		e of silic						
				er grade		Γ	08 = 8	300 V	7
	6 -		-	le x 100	= V _{RRM}		12 = 1	200 V	
	7 -		PAK	4 - 1 - 12 - 24		L			
	8 -			tal digit:					
		-M3	= halog	en-free,	RoHS-0	compliar	nt, and t	erminat	ions lea

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-16TTS08FP-M3	50	1000	Antistatic plastic tubes				
VS-16TTS12FP-M3	50	1000	Antistatic plastic tubes				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96155				
Part marking information	www.vishay.com/doc?95456				

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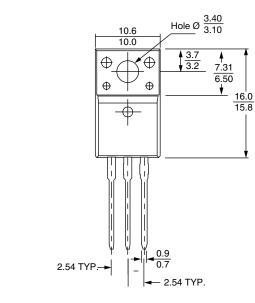
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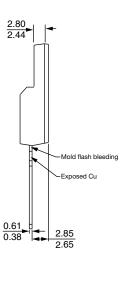


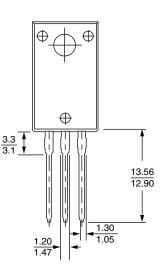
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3L TO-220 FullPAK

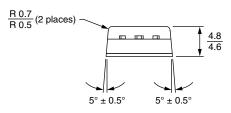
DIMENSIONS in millimeters







Bottom view



Notes

- ⁽¹⁾ All dimensions are in mm
- ⁽²⁾ Package body size exclude mold flash and burrs. Moldflash should be less than 6 mils



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